

Session TH3B

Nonlinear Transistor Modeling

Chairman:

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Large-signal heterojunction bipolar transistor models have been further developed to include temperature dependence and intermodulation distortion. Waveform characterization is shown as a viable technique to gain insight into transistor current-voltage characteristics. A systematic approach for calculating intermodulation distortion in resistive FET mixers is presented. Inconsistency produced by transcapacitance in nonlinear FET models is clarified.

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1:30 p.m.-3:00 p.m., Thursday, May 18, 1995
Room A2